



**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	60	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 7) V <sub>GS</sub> = 10V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	5.0 4.0	A
	t < 10s	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	6.3 5.0	A
Continuous Drain Current (Note 7) V <sub>GS</sub> = 5V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	4.3 3.4	A
	t < 10s	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	5.4 4.3	A
Maximum Body Diode Forward Current (Note 7)			I <sub>S</sub>	2.1	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	30	A
Avalanche Current (Note 8) L = 0.1mH			I <sub>AR</sub>	14.2	A
Avalanche Energy (Note 8) L = 0.1mH			E <sub>AR</sub>	10	mJ

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P <sub>D</sub>	1.2	W
	T <sub>A</sub> = +70°C		0.75	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>θJA</sub>	106	°C/W
	t < 10s		69	°C/W
Total Power Dissipation (Note 7)	T <sub>A</sub> = +25°C	P <sub>D</sub>	1.8	W
	T <sub>A</sub> = +70°C		1.1	
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	R <sub>θJA</sub>	68	°C/W
	t < 10s		44	°C/W
Thermal Resistance, Junction to Case (Note 7)		R <sub>θJC</sub>	20	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

- Notes:
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  8. I<sub>AR</sub> and E<sub>AR</sub> rating are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.

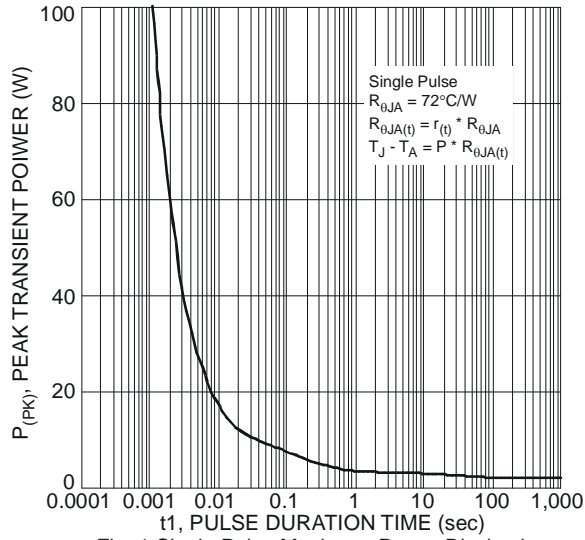


Fig. 1 Single Pulse Maximum Power Dissipation

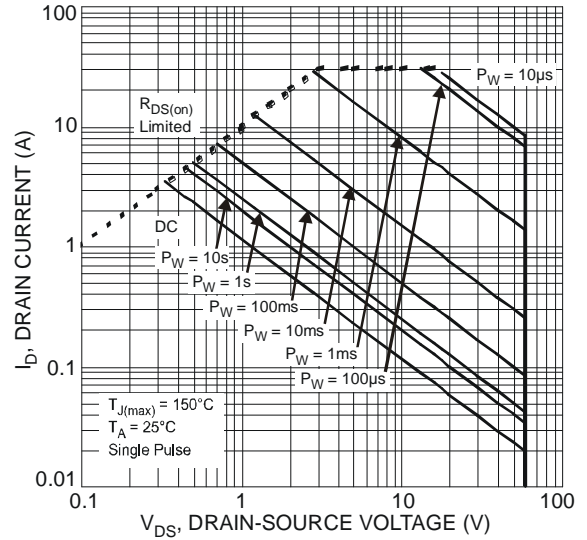


Fig. 2 SOA, Safe Operation Area

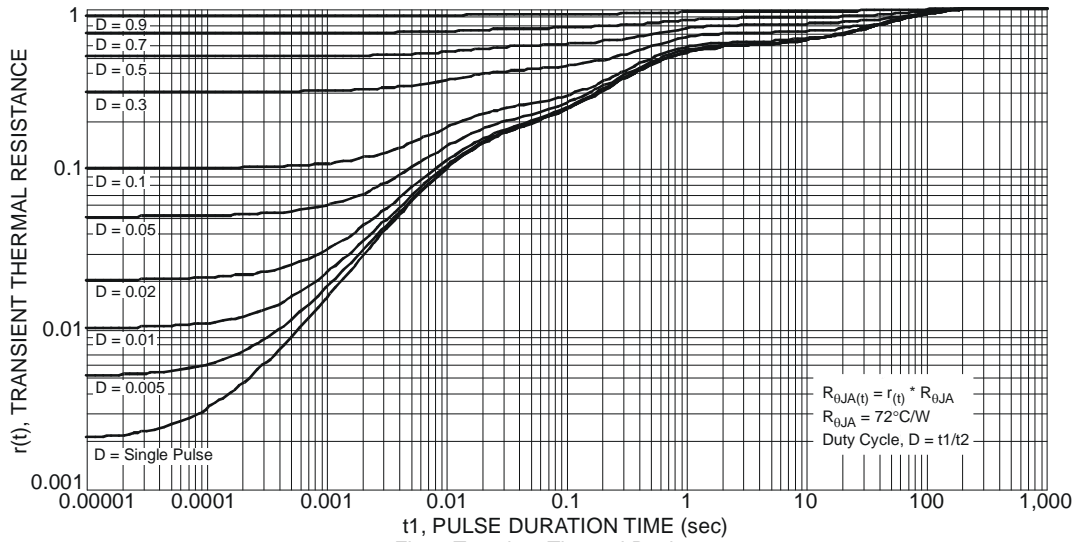


Fig. 3 Transient Thermal Resistance

**Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 9)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	100	nA	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b> (Note 9)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	—	3	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	30	44	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 4.3A
		—	35	60		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 4A
Forward Transfer Admittance	Y <sub>FS</sub>	—	4.5	—	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 4.3A
Diode Forward Voltage	V <sub>SD</sub>	—	0.7	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1A
<b>DYNAMIC CHARACTERISTICS</b> (Note 10)						
Input Capacitance	C <sub>ISS</sub>	—	1,287	—	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>OSS</sub>	—	57	—		
Reverse Transfer Capacitance	C <sub>RSS</sub>	—	44	—		
Gate Resistance	R <sub>G</sub>	—	1.2	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>G</sub>	—	22.4	—	nC	V <sub>DS</sub> = 30V, I <sub>D</sub> = 4.3A
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>G</sub>	—	10.4	—		
Gate-Source Charge	Q <sub>GS</sub>	—	4.9	—		
Gate-Drain Charge	Q <sub>GD</sub>	—	3.0	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	6.6	—	ns	V <sub>GS</sub> = 10V, V <sub>DD</sub> = 30V, R <sub>G</sub> = 6Ω, I <sub>D</sub> = 4.3A
Turn-On Rise Time	t <sub>R</sub>	—	8.1	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	20.1	—		
Turn-Off Fall Time	t <sub>F</sub>	—	4.0	—		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	—	18	—	ns	I <sub>S</sub> = 4.3A, dI/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	—	11.9	—	nC	I <sub>S</sub> = 4.3A, dI/dt = 100A/μs

Notes: 9. Short duration pulse test used to minimize self-heating effect.  
10. Guaranteed by design. Not subject to product testing.

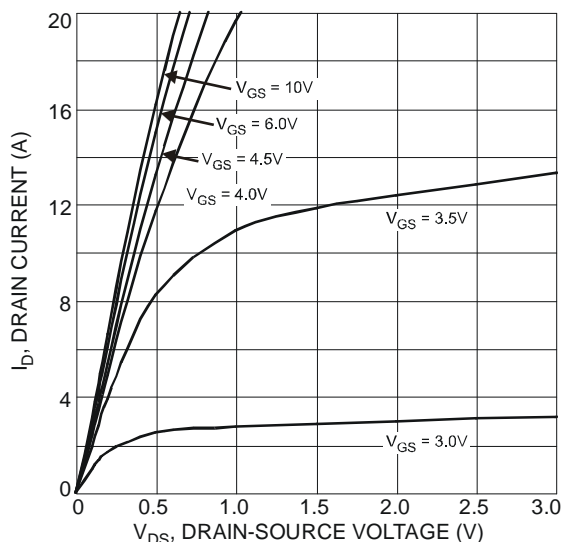


Fig. 4 Typical Output Characteristic

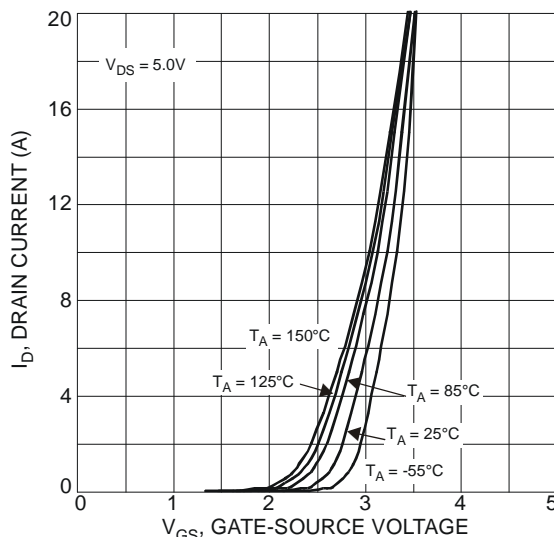


Fig. 5 Typical Transfer Characteristics

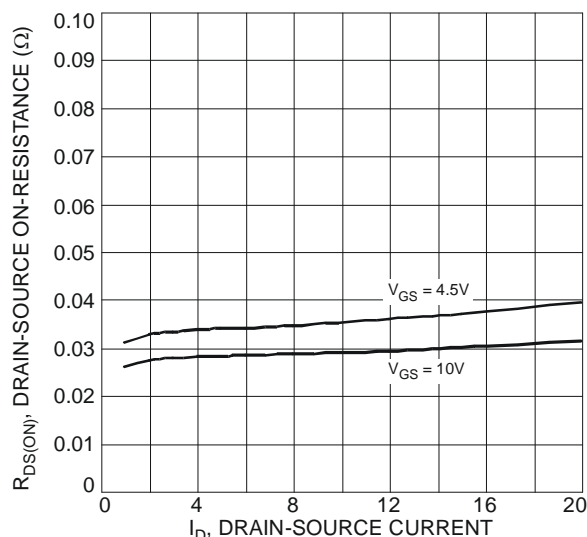


Fig. 6 Typical On-Resistance vs. Drain Current and Gate Voltage

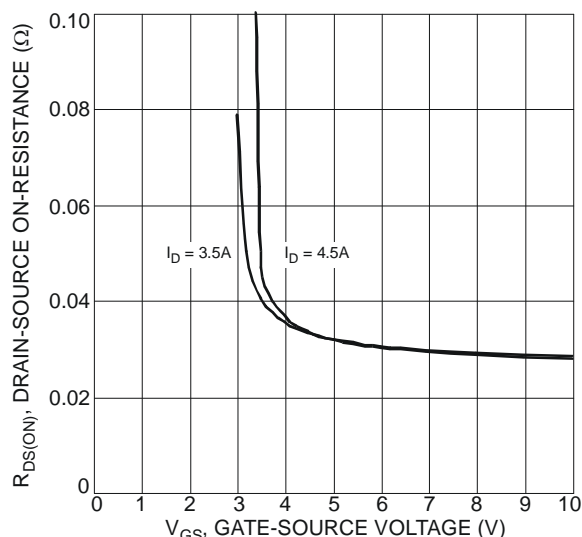


Fig. 7 Typical On-Resistance vs. Drain Current and Gate Voltage

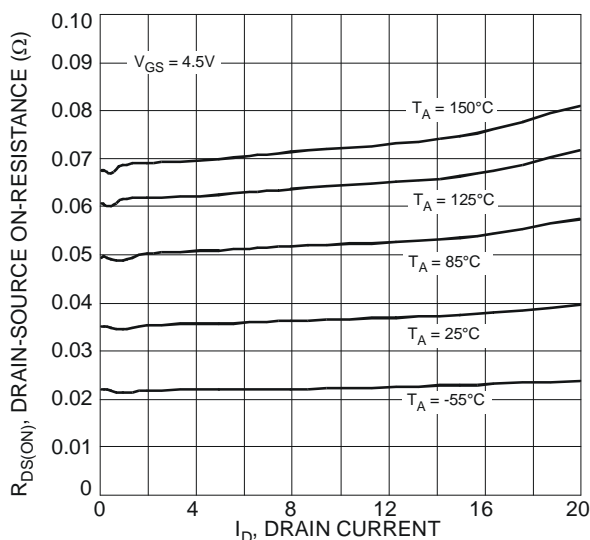


Fig. 8 Typical On-Resistance vs. Drain Current and Temperature

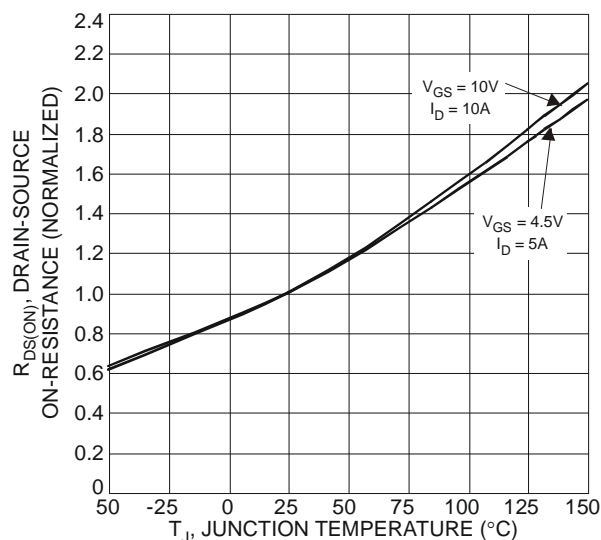


Fig. 9 On-Resistance Variation with Temperature

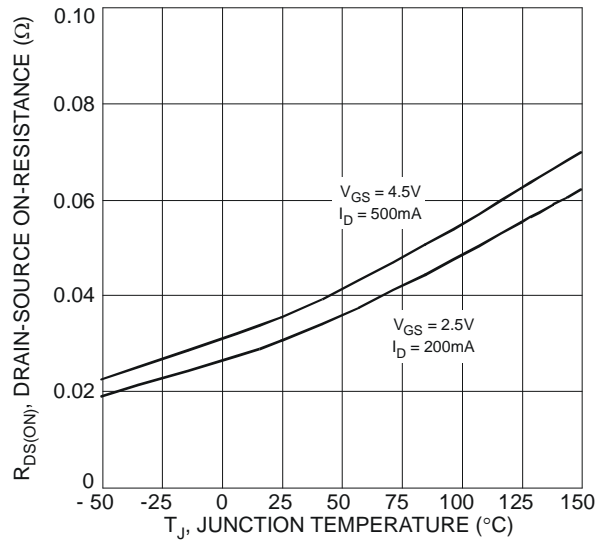


Fig. 10 On-Resistance Variation with Temperature

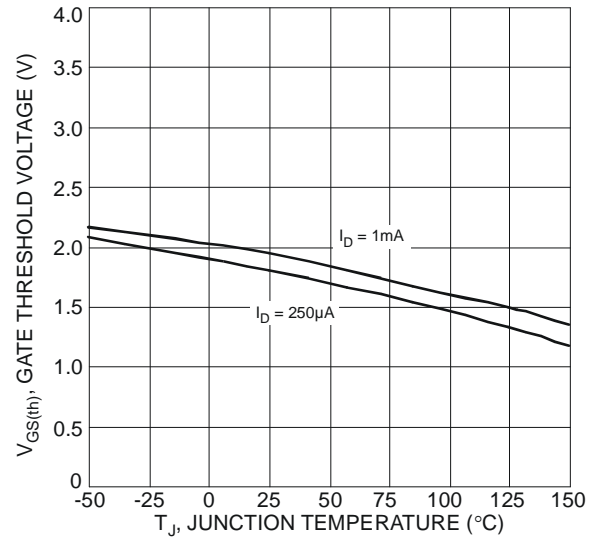


Fig. 11 Gate Threshold Variation vs. Ambient Temperature

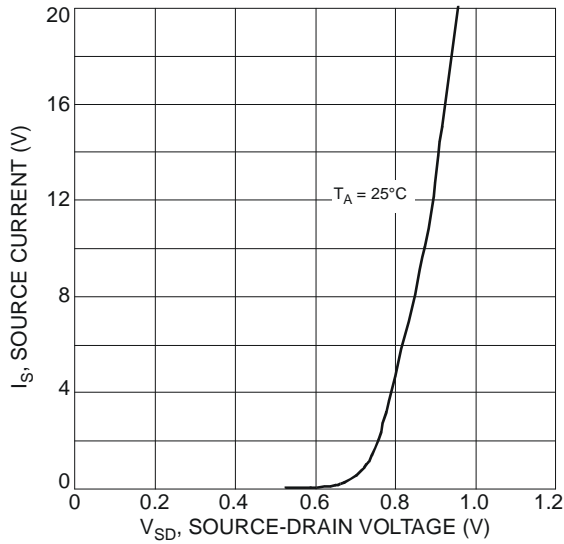


Fig. 12 Diode Forward Voltage vs. Current

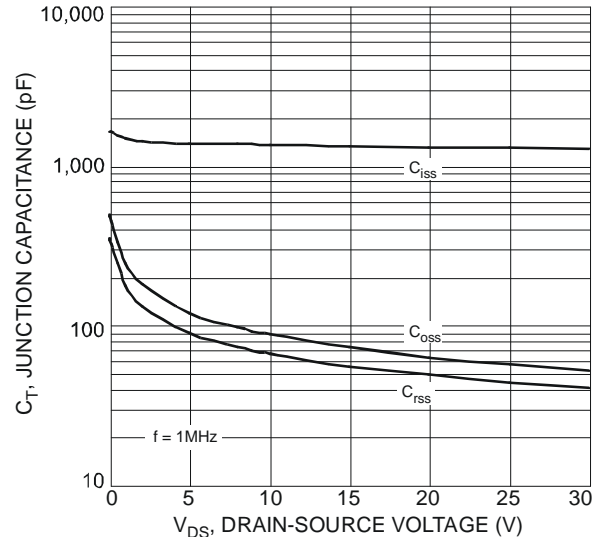


Fig. 13 Typical Junction Capacitance

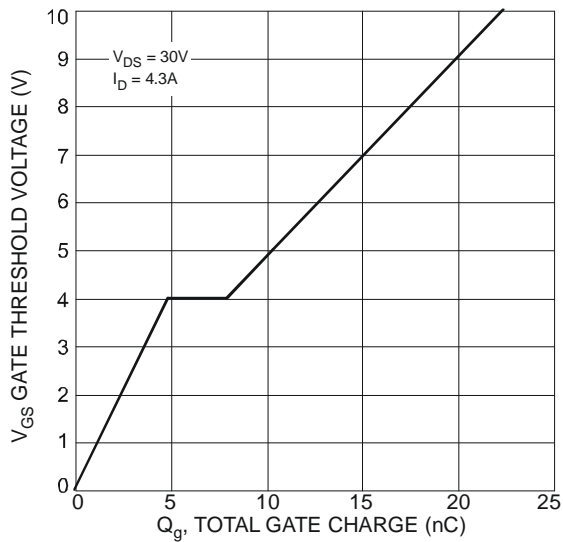
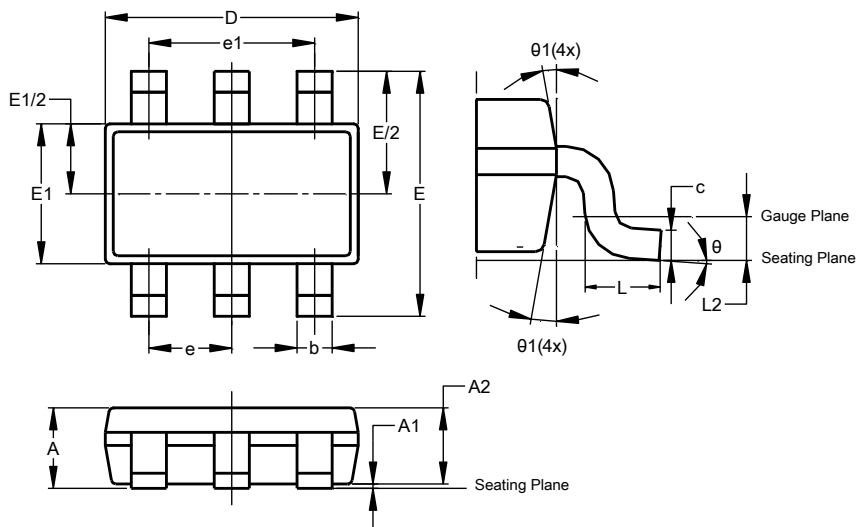


Fig. 14 Gate Charge

## Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

TSOT26

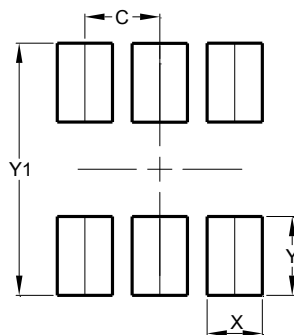


TSOT26			
Dim	Min	Max	Typ
A	—	1.00	—
A1	0.010	0.100	—
A2	0.840	0.900	—
D	2.800	3.000	2.900
E	2.800 BSC		
E1	1.500	1.700	1.600
b	0.300	0.450	—
c	0.120	0.200	—
e	0.950 BSC		
e1	1.900 BSC		
L	0.30	0.50	—
L2	0.250 BSC		
θ	0°	8°	4°
θ1	4°	12°	—
All Dimensions in mm			

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.

TSOT26



Dimensions	Value (in mm)
C	0.950
X	0.700
Y	1.000
Y1	3.199

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